# 2SA1816(Tentative)

### Silicon PNP epitaxial planer type

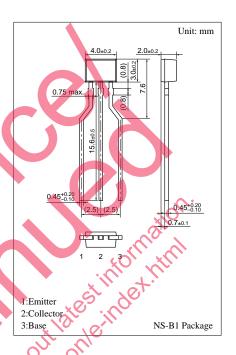
For low-frequency high breakdown voltage amplification

#### Features

• High collector to emitter voltage V<sub>CEO</sub>.

#### Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	-150	У
Collector to emitter voltage	V <sub>CEO</sub>	-150	V
Emitter to base voltage	V <sub>EBO</sub>	-5	V
Peak collector current	I <sub>CP</sub>	-100	mA
Collector current	$I_{C}$	-50	mA
Collector power dissipation	P <sub>C</sub>	300	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	<b>−</b> 55 ~ +150	°C



#### Electrical Characteristics (Ta=25°C

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{\rm CB} = -100 V$ , $I_{\rm E} = 0$			-1	μА
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = -100 \mu A, I_{\rm B} = 0$	-150			V
Emitter to base voltage	$V_{\rm EBO}$	$I_{\rm E} = -10\mu A, I_{\rm C} = 0$	-5			V
Forward current transfer ratio	h <sub>FE</sub> *1	$V_{CE} = -5V, I_{C} = -10\text{mA}$	90		450	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -30  {\rm mA}, I_{\rm B} = -3  {\rm mA}$			-1	V
Transition frequency	f <sub>T</sub>	$V_{CB} = -10V$ , $I_E = 10$ mA, $f = 200$ MHz		200		MHz
Collector output capacitance	Copy	$V_{CB} = -10V, I_E = 0, f = 1MHz$			5	pF
Noise voltage	NV	$V_{CE} = -10V, I_C = -1mA, G_V = 80dB$	150			mV
	1 <b>V</b> V	$R_g = 100 k\Omega$ , Function = FLAT		130	130	III V

<sup>\*1</sup>hFE Rank classification

Rank	Q	R	S	T
$h_{FE}$	90 ~ 155	130 ~ 220	185 ~ 330	260 ~ 450

160 Panasonic

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